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(54) Title: A METHOD FOR MAKING A SEMICONDUCTOR DEVICE HAVING A HIGH-K GATE DIELECTRIC

(57) Abstract: A method for making a semiconductor device is described. That method comprises forming on a substrate a dielectric layer that has a dielectric constant that is greater than the dielectric constant of silicon dioxide. An insulating layer, which is compatible with the dielectric layer and a gate electrode to be formed on the insulating layer, is formed on the dielectric layer, and a gate electrode is then formed on the insulating layer.